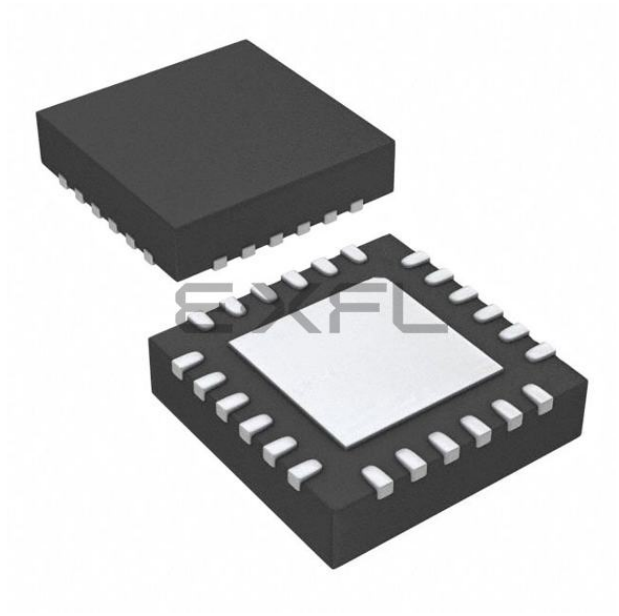
Silicon Labs - EFM32TG110F4-QFN24T Datasheet



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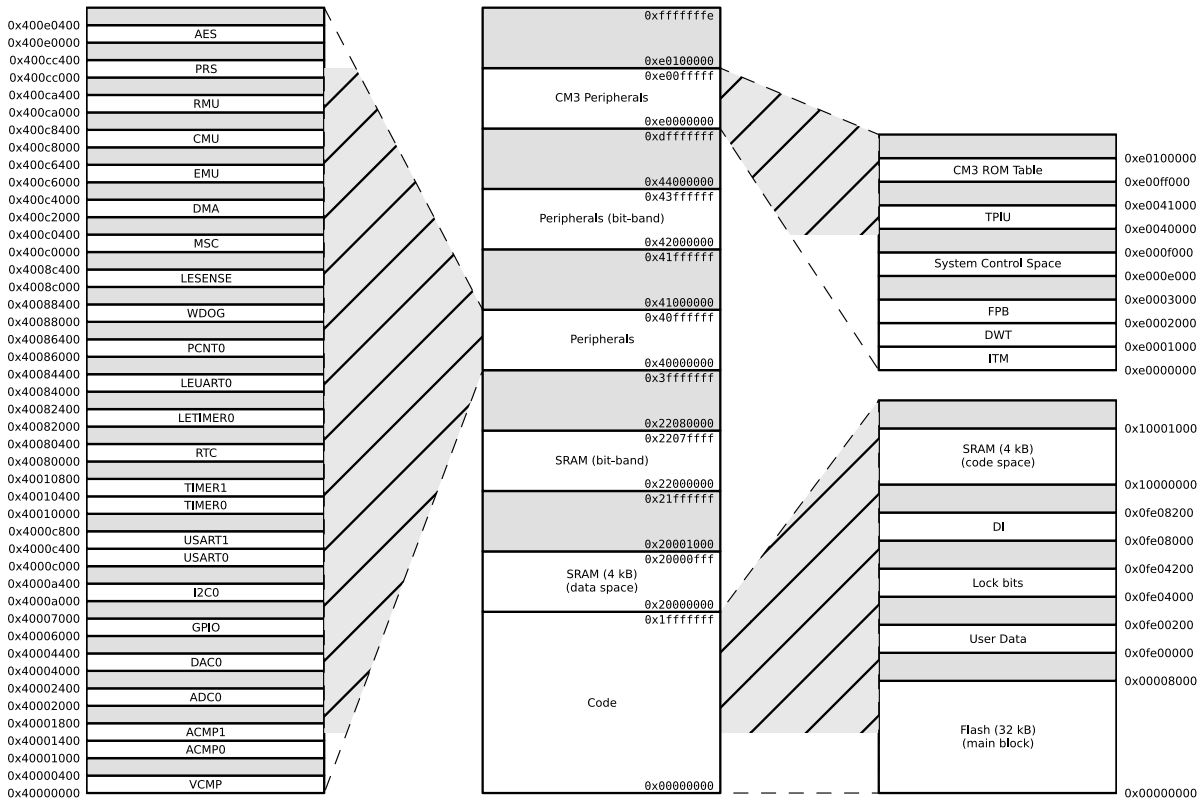
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	17
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 2x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VQFN Exposed Pad
Supplier Device Package	24-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg110f4-qfn24t

Figure 2.2. EFM32TG110 Memory Map with largest RAM and Flash sizes



3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 9), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 9), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 9) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 9) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150[1]	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V

[1]Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			32	MHz
f_{AHB}	Internal AHB clock frequency			32	MHz

3.4 Current Consumption

Table 3.3. Current Consumption

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{EM0}	EM0 current. No prescaling. Running prime number calculation code from Flash. (Production test condition = 14 MHz)	32 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V		157		µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		150	170	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		153	172	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		155	175	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		157	178	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		162	183	µA/MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		200	240	µA/MHz
I_{EM1}	EM1 current (Production test condition = 14 MHz)	32 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V		53		µA/MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		51	57	µA/MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		55	59	µA/MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		56	61	µA/MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		58	63	µA/MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		63	68	µA/MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD}= 3.0 V		100	122	µA/MHz
I_{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=25°C		1.0	1.2	µA
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		2.4	5.0	µA
I_{EM3}	EM3 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.59	1.0	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		2.0	4.5	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.055	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.25	0.70	µA

Figure 3.1. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.

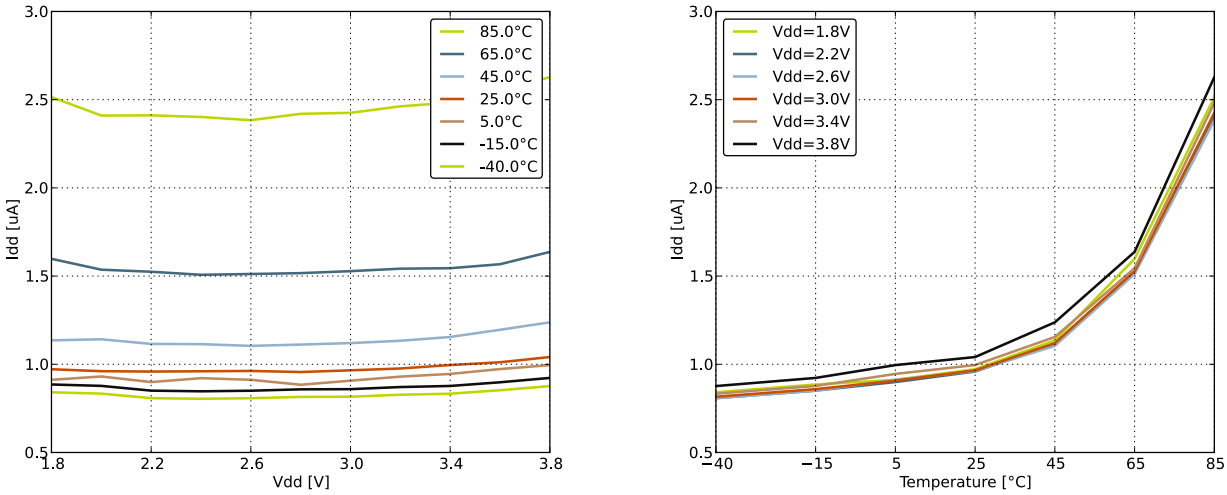


Figure 3.2. EM3 current consumption.

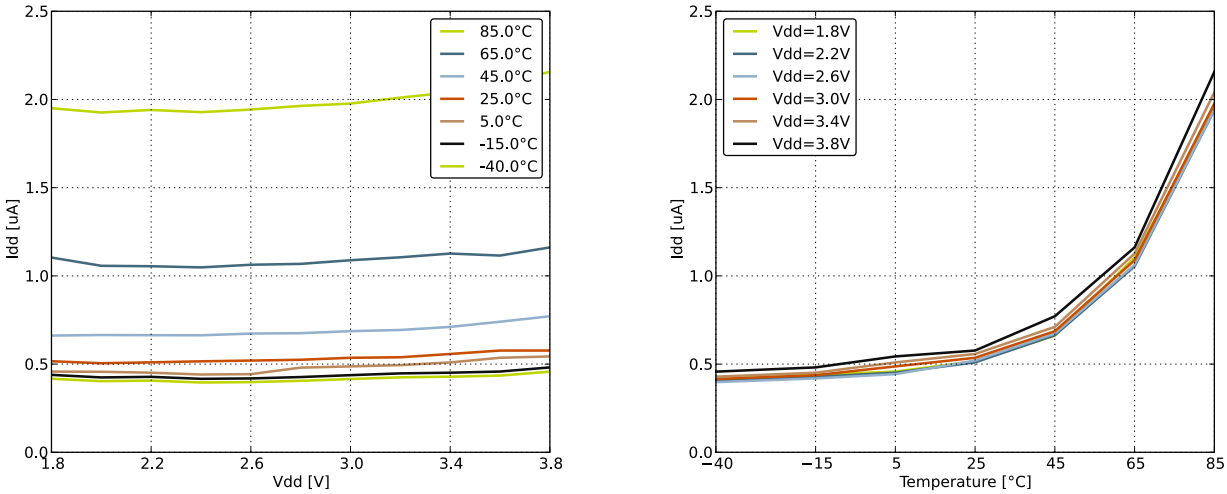


Figure 3.3. EM4 current consumption.

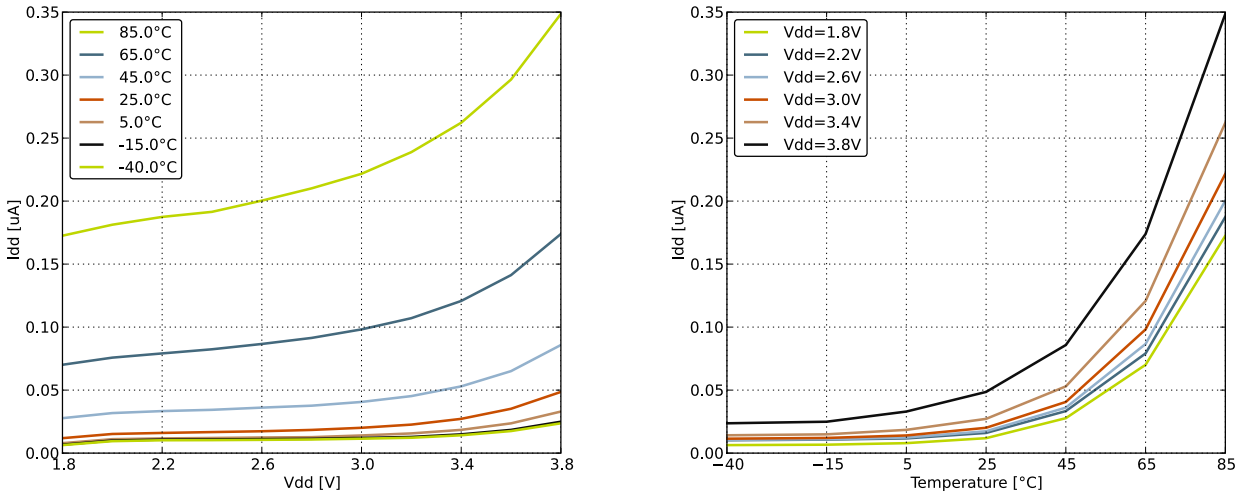
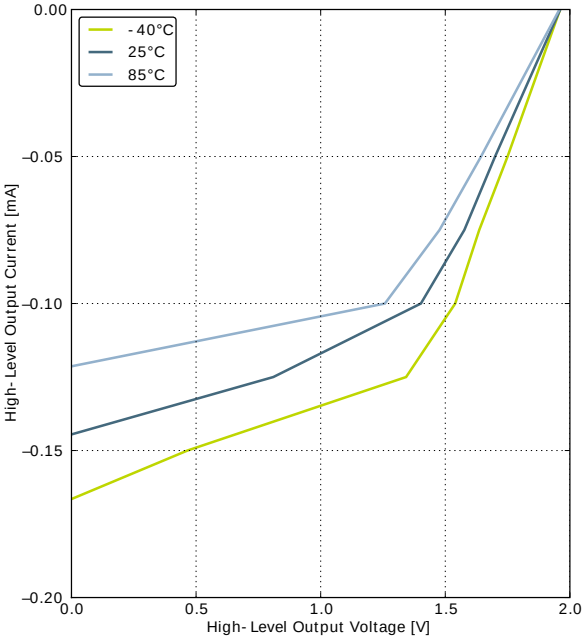
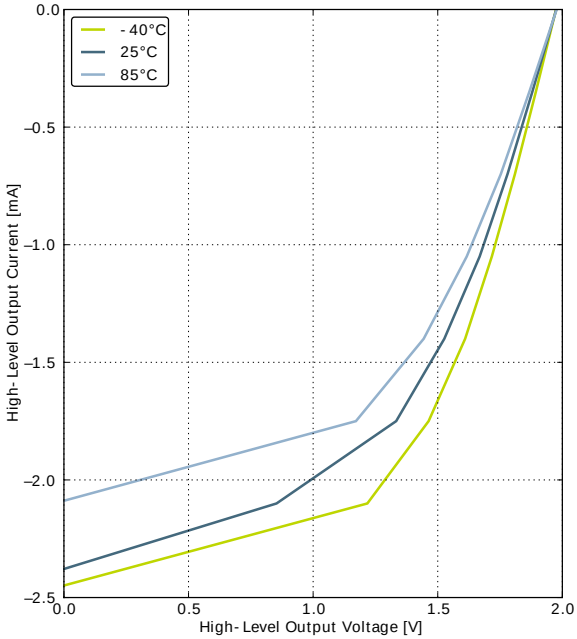


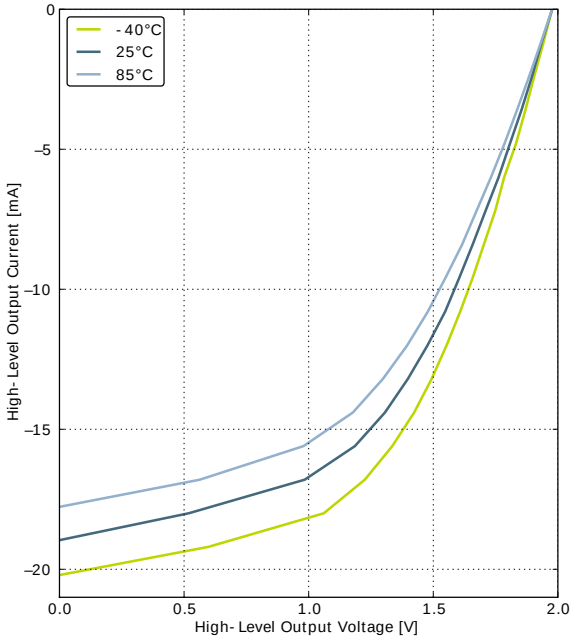
Figure 3.5. Typical High-Level Output Current, 2V Supply Voltage



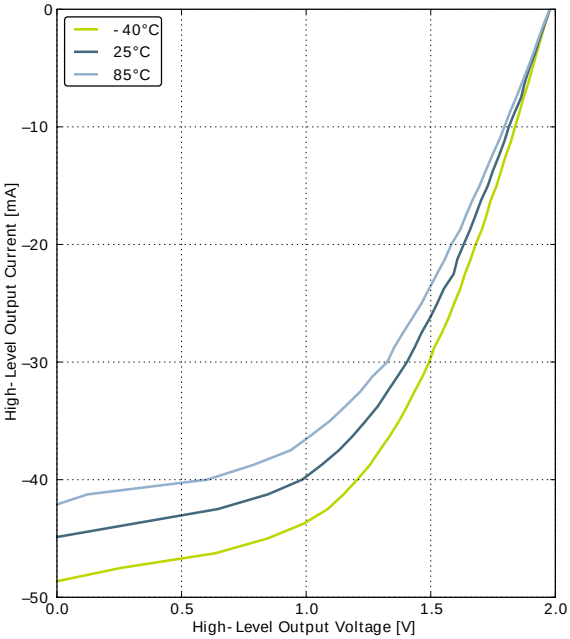
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

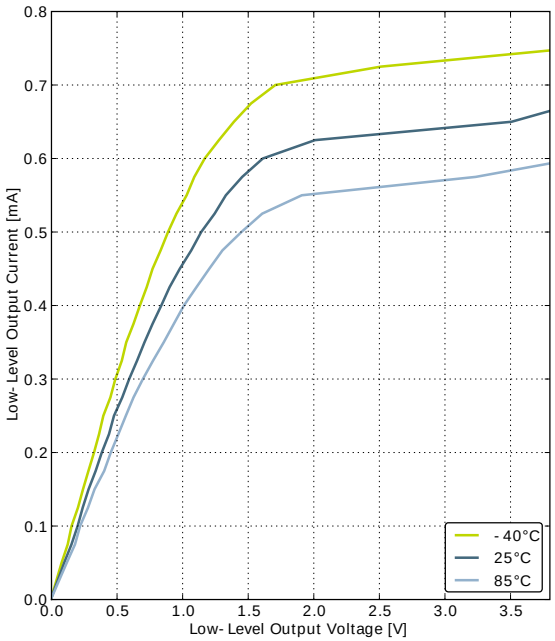


GPIO_Px_CTRL DRIVEMODE = STANDARD

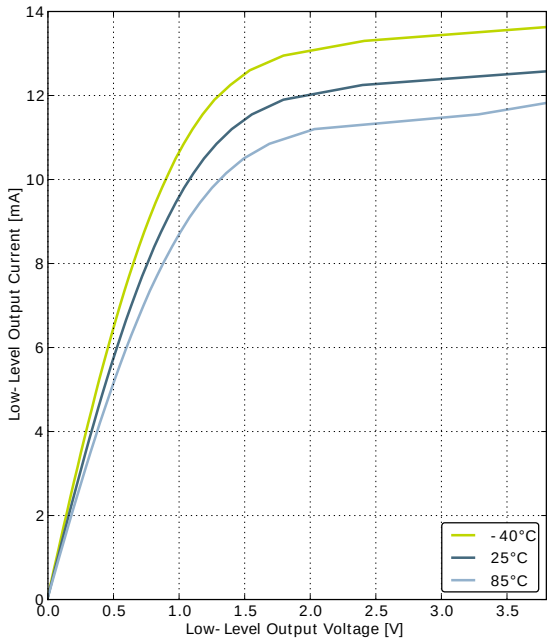


GPIO_Px_CTRL DRIVEMODE = HIGH

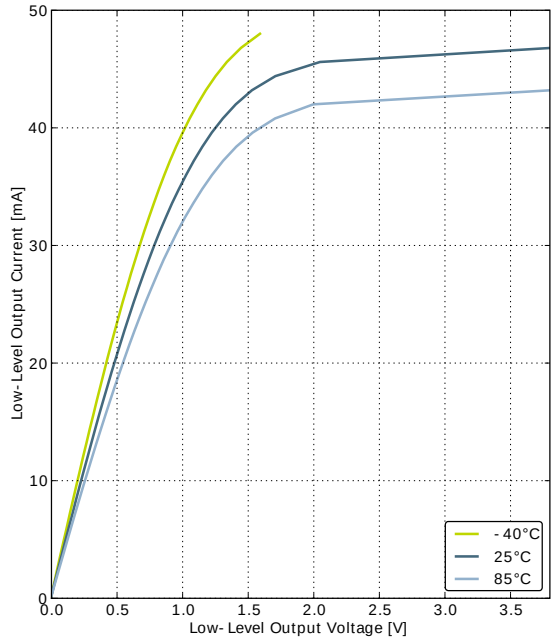
Figure 3.8. Typical Low-Level Output Current, 3.8V Supply Voltage



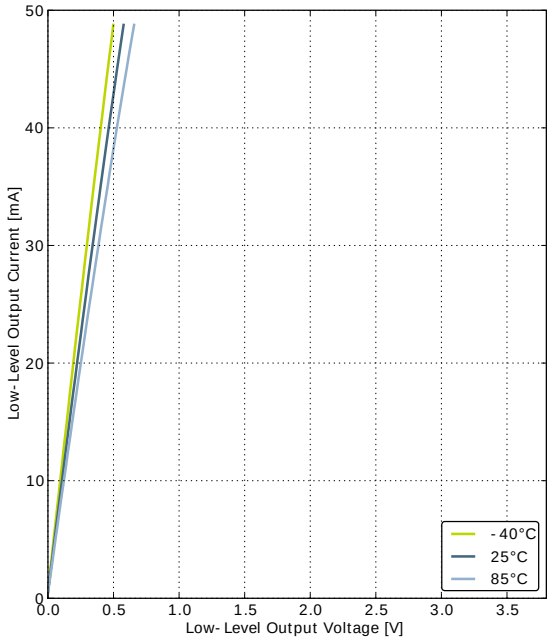
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		f_{HFRCO} = 14 MHz		104	120	µA
		f_{HFRCO} = 11 MHz		94	110	µA
		f_{HFRCO} = 6.6 MHz		63	90	µA
		f_{HFRCO} = 1.2 MHz		22	32	µA
$TUNESTEP_{H-FRCO}$	Frequency step for LSB change in TUNING value			0.3[3]		%

[1]For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

[2]For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

[3]The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.11. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

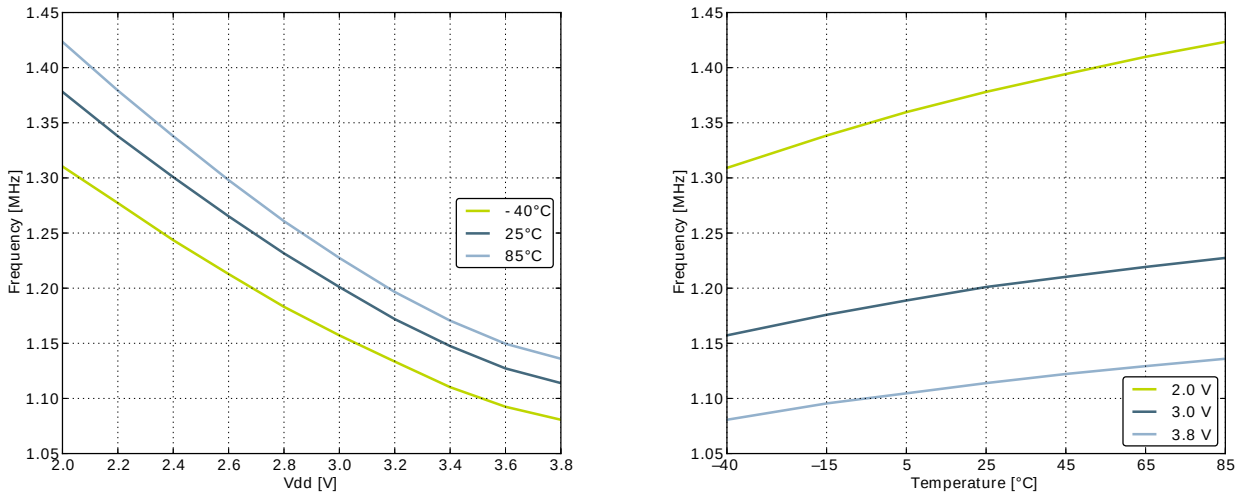


Figure 3.12. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

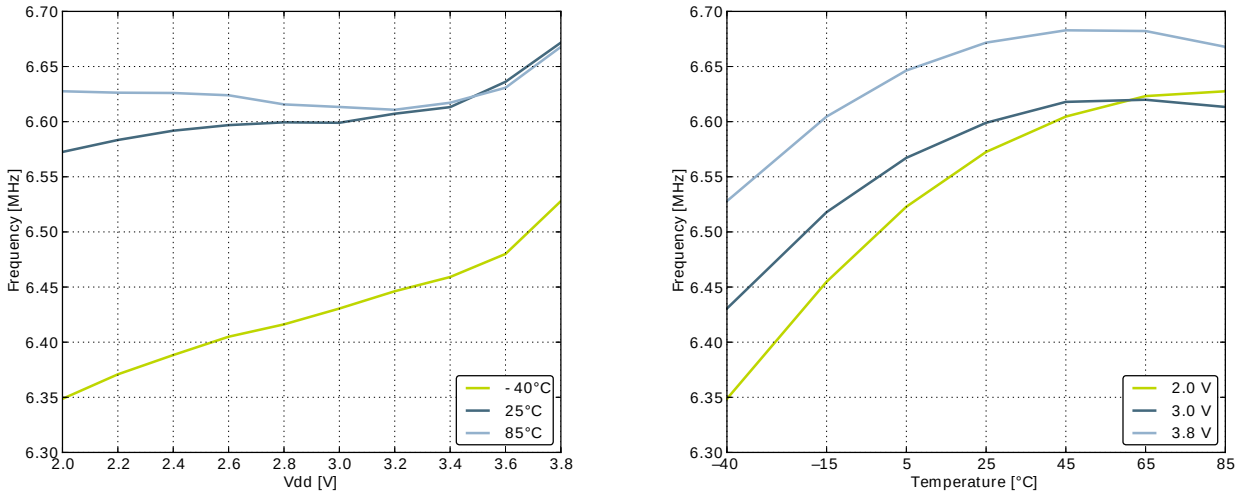
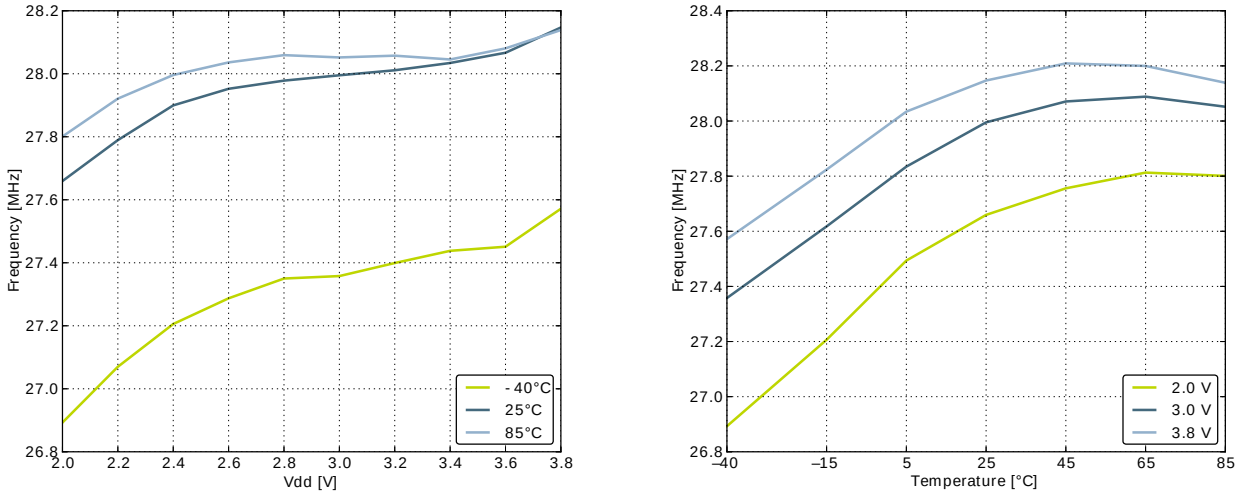


Figure 3.16. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature



3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$f_{AUXHFRCO}$	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	28 MHz frequency band	27.16	28.0	28.84	MHz
		21 MHz frequency band	20.37	21.0	21.63	MHz
		14 MHz frequency band	13.58	14.0	14.42	MHz
		11 MHz frequency band	10.67	11.0	11.33	MHz
		7 MHz frequency band	6.40[1]	6.60[1]	6.80[1]	MHz
		1 MHz frequency band	1.16[2]	1.20[2]	1.24[2]	MHz
$t_{AUXHFRCO\_settling}$	Settling time after start-up	$f_{AUXHFRCO}$ = 14 MHz		0.6		Cycles
$TUNESTEP_{AUX-HFRCO}$	Frequency step for LSB change in TUNING value			0.3[3]		%

[1]For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

[2]For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

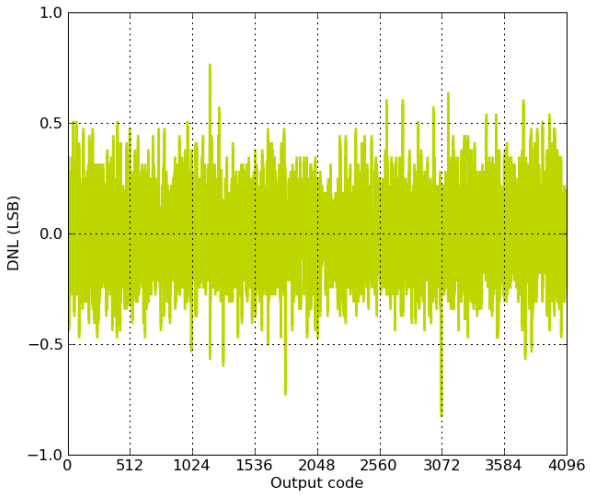
[3]The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

3.9.6 ULFRCO

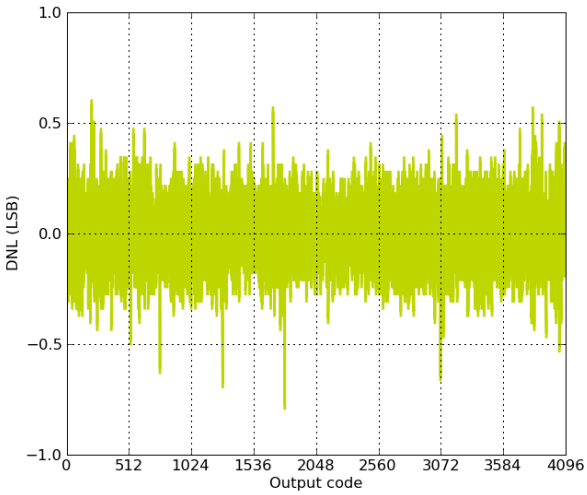
Table 3.13. ULFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ULFRCO}	Oscillation frequency	25°C, 3V	0.70		1.75	kHz
TC_{ULFRCO}	Temperature coefficient			0.05		%/°C
VC_{ULFRCO}	Supply voltage coefficient			-18.2		%/V

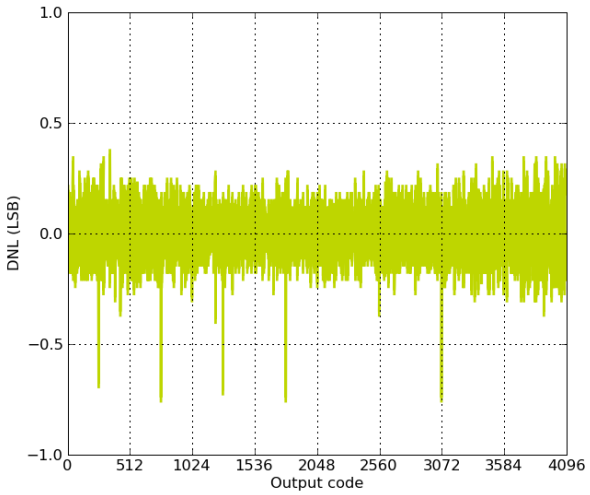
Figure 3.21. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C



1.25V Reference

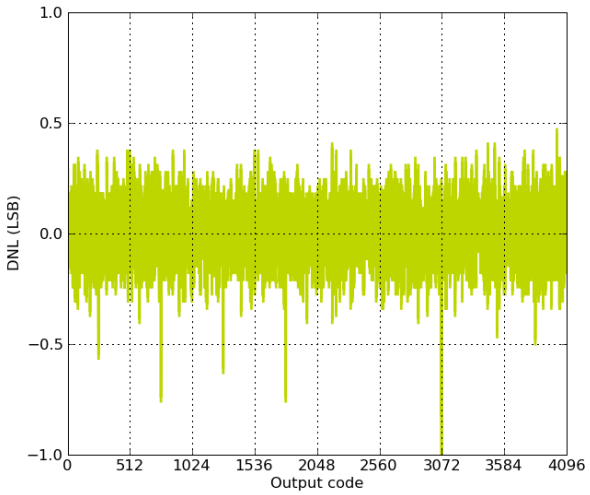


2.5V Reference



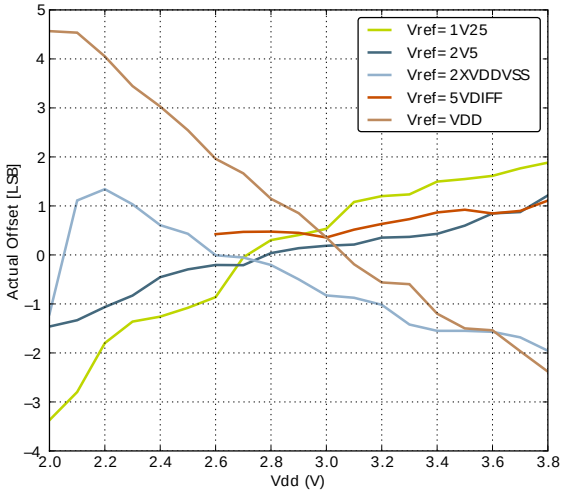
2XVDDVSS Reference

5VDIFF Reference

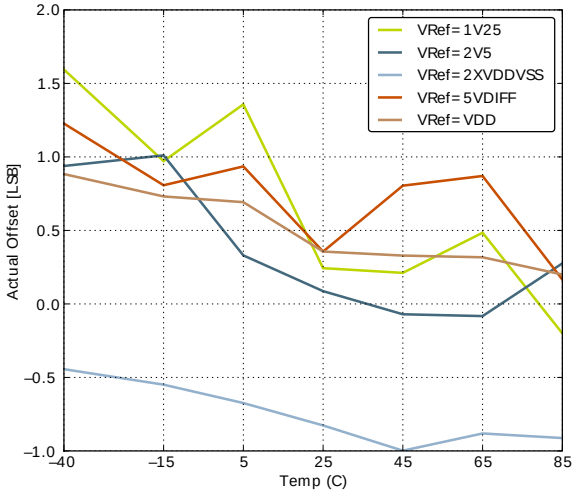


VDD Reference

Figure 3.22. ADC Absolute Offset, Common Mode = Vdd /2

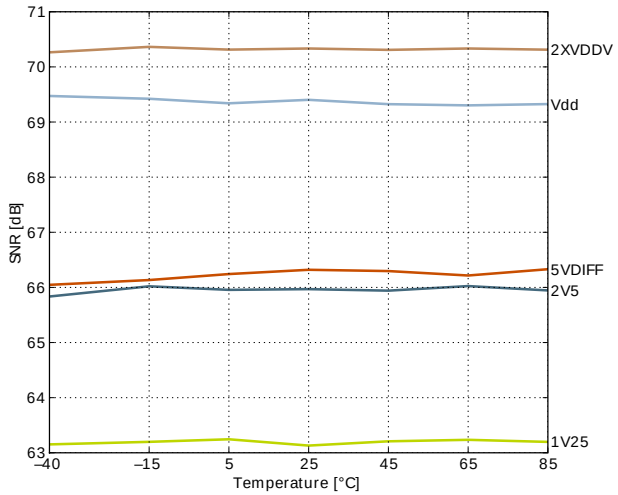


Offset vs Supply Voltage, Temp = 25°C

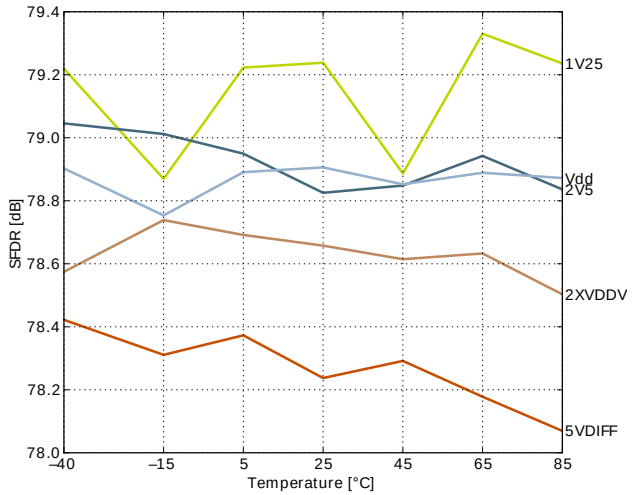


Offset vs Temperature, Vdd = 3V

Figure 3.23. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V



Signal to Noise Ratio (SNR)



Spurious-Free Dynamic Range (SFDR)

3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12bit		400	650	µA
		100 kSamples/s, 12 bit		200	250	µA
		1 kSamples/s 12 bit NORMAL		17	25	µA
SR_{DAC}	Sample rate				500	ksamples/s

Symbol	Parameter	Condition	Min	Typ	Max	Unit
PU_{OPAMP}	Power-up Time	OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		0.09		µs
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		1.52		µs
		OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		12.74		µs
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		0.09		µs
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		0.13		µs
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.17		µs
N_{OPAMP}	Voltage Noise	V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=0		101		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx-HCMDIS=1		141		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		196		μV_{RMS}
		V_{out}=1V, RESSEL=0, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAxHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=0		1630		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAxHCMDIS=1		2590		μV_{RMS}

Figure 3.24. OPAMP Common Mode Rejection Ratio

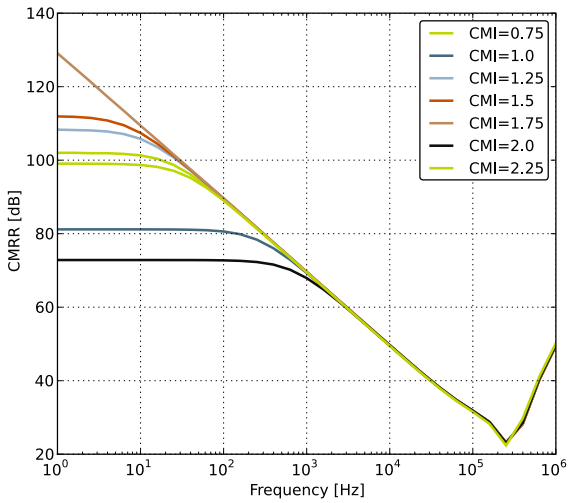
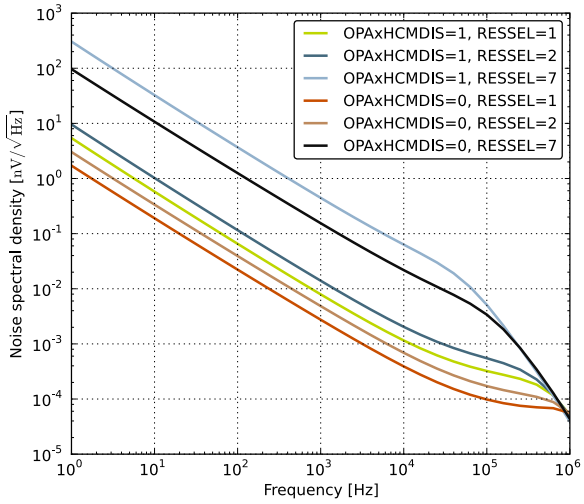


Figure 3.28. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)



3.14 Voltage Comparator (VCMP)

Table 3.18. VCMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{VCMPIN}	Input voltage range			V_{DD}		V
V_{VCMPCM}	VCMP Common Mode voltage range			V_{DD}		V
I_{VCMP}	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	0.6	µA
		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	30	µA
$t_{VCMPREF}$	Startup time reference generator	NORMAL		10		µs
$V_{VCMPOFFSET}$	Offset voltage	Single ended		10		mV
		Differential		10		mV
$V_{VCMPHYST}$	VCMP hysteresis			17		mV
$t_{VCMPSTART}$	Startup time				10	µs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

$$V_{DD\ Trigger\ Level}=1.667V+0.034 \times TRIGLEVEL \quad (3.2)$$

3.15 I2C

Table 3.19. I2C Standard-mode (Sm)

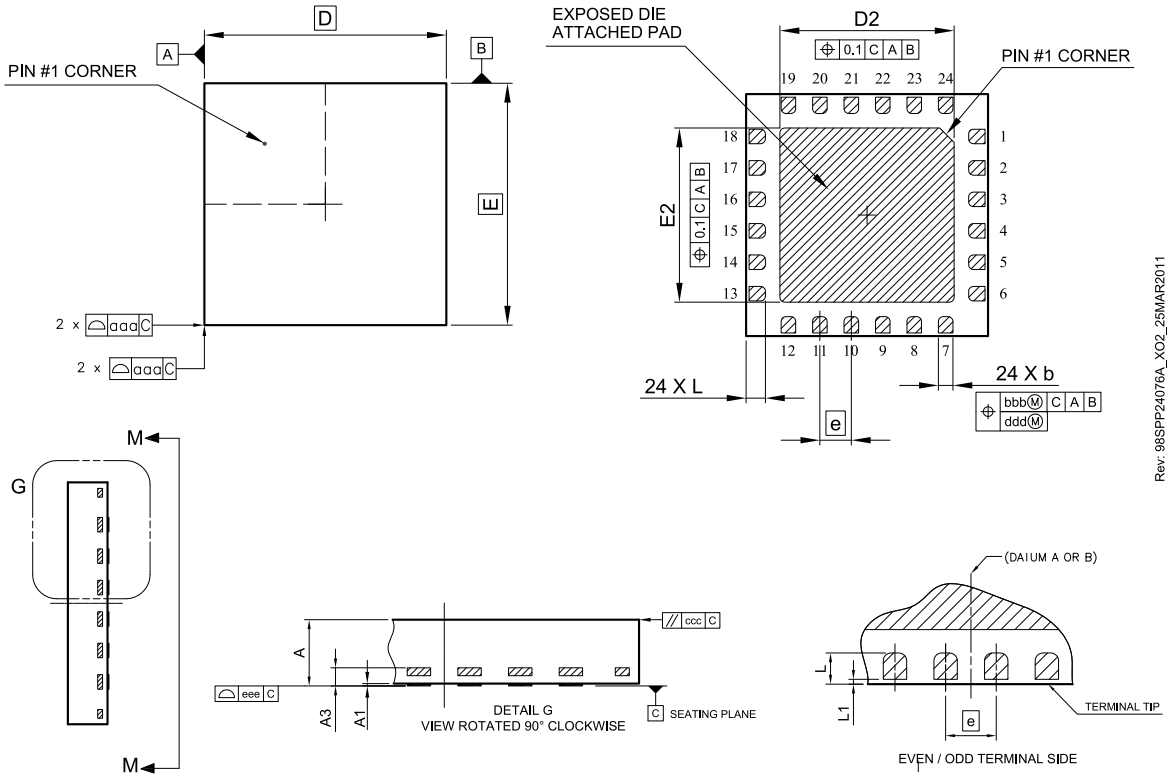
Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		100[1]	kHz
t_{LOW}	SCL clock low time	4.7			µs
t_{HIGH}	SCL clock high time	4.0			µs
$t_{SU,DAT}$	SDA set-up time	250			ns
$t_{HD,DAT}$	SDA hold time	8		3450[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	4.7			µs
$t_{HD,STA}$	(Repeated) START condition hold time	4.0			µs
$t_{SU,STO}$	STOP condition set-up time	4.0			µs
t_{BUF}	Bus free time between a STOP and START condition	4.7			µs

[1]For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32TG Reference Manual.
[2]The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3]When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
HFXTAL_P	PB13							High Frequency Crystal positive pin.
I2C0_SCL		PD7			PC1	PF1	PE13	I2C0 Serial Clock Line input / output.
I2C0_SDA	PA0	PD6			PC0	PF0	PE12	I2C0 Serial Data input / output.
LES_ALTEX0	PD6							LESENSE alternate exite output 0.
LES_ALTEX1	PD7							LESENSE alternate exite output 1.
LES_ALTEX6	PE12							LESENSE alternate exite output 6.
LES_ALTEX7	PE13							LESENSE alternate exite output 7.
LES_CH0	PC0							LESENSE channel 0.
LES_CH1	PC1							LESENSE channel 1.
LES_CH14	PC14							LESENSE channel 14.
LES_CH15	PC15							LESENSE channel 15.
LETIM0_OUT0	PD6	PB11	PF0					Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	PD7		PF1					Low Energy Timer LETIM0, output channel 1.
LEU0_RX		PB14		PF1	PA0			LEUART0 Receive input.
LEU0_TX		PB13		PF0	PF2			LEUART0 Transmit output. Also used as receive input in half duplex communication.
LFXTAL_N	PB8							Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.
LFXTAL_P	PB7							Low Frequency Crystal (typically 32.768 kHz) positive pin.
PCNT0_S0IN			PC0	PD6				Pulse Counter PCNT0 input number 0.
PCNT0_S1IN	PC14		PC1	PD7				Pulse Counter PCNT0 input number 1.
PRS_CH0	PA0							Peripheral Reflex System PRS, channel 0.
PRS_CH2	PC0							Peripheral Reflex System PRS, channel 2.
PRS_CH3	PC1							Peripheral Reflex System PRS, channel 3.
TIM0_CC0	PA0	PA0			PA0	PF0		Timer 0 Capture Compare input / output channel 0.
TIM0_CC1					PC0	PF1		Timer 0 Capture Compare input / output channel 1.
TIM0_CC2					PC1	PF2		Timer 0 Capture Compare input / output channel 2.
TIM1_CC0				PB7	PD6			Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14			PB8	PD7			Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12		PB11				Timer 1 Capture Compare input / output channel 2.
US0_CLK	PE12			PC15	PB13	PB13		USART0 clock input / output.
US0_CS	PE13			PC14	PB14	PB14		USART0 chip select input / output.
US0_RX				PE12	PB8	PC1		USART0 Asynchronous Receive. USART0 Synchronous mode Master Input / Slave Output (MISO).
US0_TX				PE13	PB7	PC0		USART0 Asynchronous Transmit.Also used as receive input in half duplex communication. USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7		PF0					USART1 clock input / output.
US1_CS	PB8		PF1					USART1 chip select input / output.
US1_RX	PC1		PD6					USART1 Asynchronous Receive. USART1 Synchronous mode Master Input / Slave Output (MISO).

4.5 QFN24 Package

Figure 4.3. QFN24



Note:

1. Dimensioning & tolerancing confirm to ASME Y14.5M-1994.
2. All dimensions are in millimeters. Angles are in degrees.
3. Dimension 'b' applies to metallized terminal and is measured between 0.25 mm and 0.30 mm from the terminal tip. Dimension L1 represents terminal full back from package edge up to 0.1 mm is acceptable.
4. Coplanarity applies to the exposed heat slug as well as the terminal.
5. Radius on terminal is optional

Table 4.4. QFN24 (Dimensions in mm)

Symbol	A	A1	A3	b	D	E	D2	E2	e	L	L1	aaa	bbb	ccc	ddd	eee
Min	0.80	0.00	0.203 REF	0.25	5.00 BSC	5.00 BSC	3.50	3.50	0.65 BSC	0.35	0.00	0.10	0.10	0.10	0.05	0.08
Nom	0.85	-		0.30			3.60	3.60		0.40						
Max	0.90	0.05		0.35			3.70	3.70		0.45	0.10					

The QFN24 Package uses Nickel-Palladium-Gold preplated leadframe.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).

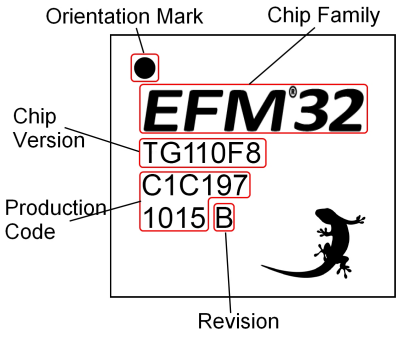
For additional Quality and Environmental information, please see:
http://www.silabs.com/support/quality/pages/default.aspx

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 54) .

6.3 Errata

Please see the errata document for EFM32TG110 for description and resolution of device erratas. This document is available in Simplicity Studio and online at: http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit

7 Revision History

7.1 Revision 1.40

March 6th, 2015

Updated Block Diagram.

Updated Energy Modes current consumption.

Updated Power Management section.

Updated LFRCO and HFRCO sections.

Added AUXHFRCO to block diagram and Electrical Characteristics.

Corrected unit to kHz on LFRCO plots y-axis.

Updated ADC section and added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Updated DAC section and added clarification on conditions for INL_{DAC} and DNL_{DAC} parameters.

Updated OPAMP section.

Updated ACMP section and the response time graph.

Updated VCMP section.

Updated Package dimensions table.

Updated Digital Peripherals section.

7.2 Revision 1.30

July 2nd, 2014

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated current consumption.

Updated transition between energy modes.

Updated power management data.

Updated GPIO data.

Updated LFXO, HFXO, HFRCO and ULFRCO data.

Updated LFRCO and HFRCO plots.

Updated ACMP data.

7.3 Revision 1.21

November 21st, 2013

Updated figures.

Updated errata-link.

B Contact Information

Silicon Laboratories Inc.
400 West Cesar Chavez
Austin, TX 78701

Please visit the Silicon Labs Technical Support web page:
http://www.silabs.com/support/pages/contacttechnicalsupport.aspx
and register to submit a technical support request.

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ARM Cortex-M0+
TINY
ARM Cortex-M3
GECKO
ARM Cortex-M3
LEOPARD
ARM Cortex-M3
GIANT
ARM Cortex-M3
WONDER
ARM Cortex-M4